



DCR960G28

Phase Control Thyristor

Replaces DS5828-1.2 DS5828-2 October 2024 (LN43617)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
DCR960G28 DCR960G26 DCR960G24	2800 2600 2400	Tvj = -40°C to 125°C, IDRM = IRRM = 50mA, VDRM, VRRM tp = 10ms VDSM & VRSM = VDRM & VRRM + 100V respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR960G28

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

\mathbf{V}_{DRM}	2800V
IT(AV)	970A
Ітѕм	13000A
dV/dt*	1500V/µs
dl/dt	500A/μs

^{*}Higher dV/dt selections are available on request

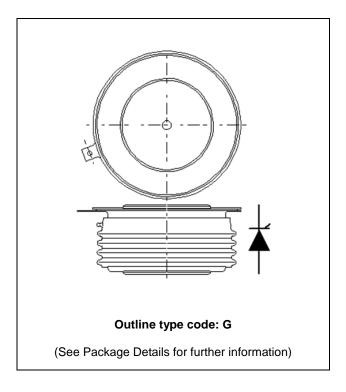


Fig. 1 Package outline

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CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
IT(AV)	Mean on-state current	Half wave resistive load	970	А
IT(RMS)	RMS value	-	1520	А
lτ	Continuous (direct) on-state current	-	1430	Α

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	13.0	kA
l²t	I2t for fusing	V _R = 0	0.85	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
	Double		DC	-	26.8	°C/kW
Rth(j-c)	Thermal resistance - junction to case	Cingle side socied	Anode DC	-	52.7	°C/kW
		Single side cooled	Cathode DC	-	65.2	°C/kW
D	Clamping force 11.5kN Thermal resistance - case to heatsink (with mounting compound)	Clamping force 11.5kN	Double side	-	7.2	°C/kW
Rth(c-h)		Single side	-	14.4	°C/kW	
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force				13	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	50	mA
Vтм	Instantaneous forward voltage	At 1600A peak, Tj = 25°C		1.50	1.65	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, g	ate open	-	1500	V/µs
dl/dt	Pote of rice of an atota gurrent	From 67% VDRM to 2x IT(AV)	Repetitive 50Hz	-	250	A/µs
di/dt	Rate of rise of on-state current	Gate source 30V, 10Ω tr < 0.5μ s, $T_j = 125$ °C	Non-repetitive	-	500	A/µs
V===	Threshold voltage - Low level	100A to 700A at Tcase = 125°C		-	0.81	\
V т(то)	Threshold voltage - High level	700A to 3000A at Tcase = 125°C		-	0.97	V
	On-state slope resistance - Low level	100A to 700A at Tcase = 12	25°C	-	0.72	mΩ
ľΤ	On-state slope resistance - High level	700A to 3000A at Tcase = 125°C		-	0.50	mΩ
t gd	Delay time	$V_D = 67\% \ V_{DRM}$, gate source 30V, 10Ω $t_T = 0.5 \mu s$, $T_j = 25 ^{\circ} C$		-	3	μs
tq	Turn-off time	T _j = 125°C, V _R = 200V, dI/dt = 5A/μs, dV _{DR} /dt = 20V/μs linear		150	350	μs
Qs	Stored charge [LEM]	Iτ = 2000A, Tj = 125°C, dl/dt = 5A/μs		700	1500	μC
IL	Latching current	Tj = 25°C, VD = 5V		-	3	А
lн	Holding current	Tj = 25°C, Rg-к = ∞, Iтм = 50	00A, Iт = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
V _{GD}	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Iст Gate trigger current VDRM = 5V, Tcase = 2		VDRM = 5V, Tcase = 25°C	250	mA
IGD	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

CURVES

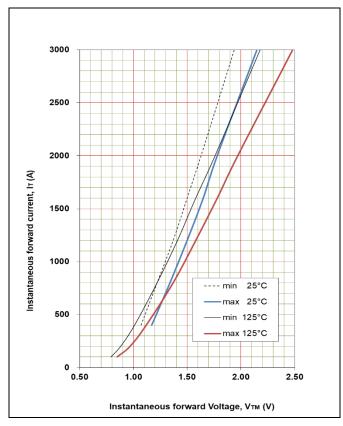


Fig. 2 Maximum & minimum on state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.226582

B = 0.140748

C = 0.000515

D = -0.007622

These values are valid for $T_j = 125$ °C for $I_T 100A$ to 3000A

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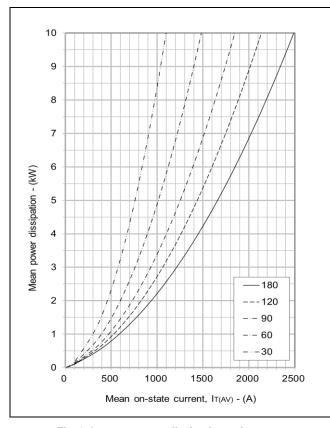


Fig. 3 On-state power dissipation - sine wave

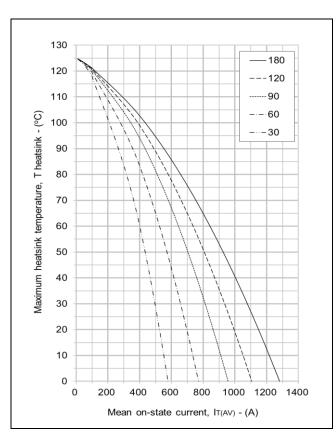


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

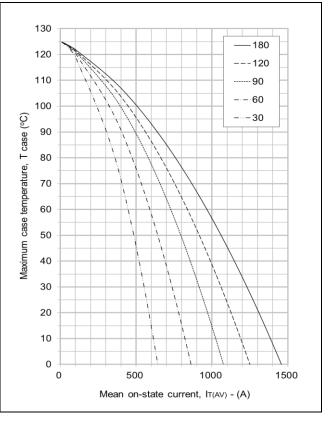


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

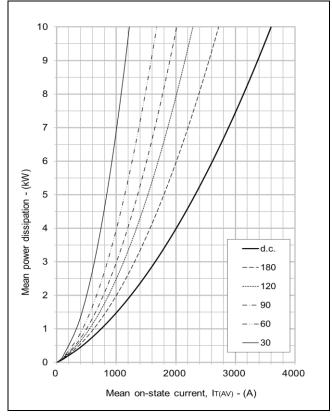


Fig. 6 On-state power dissipation - rectangular wave

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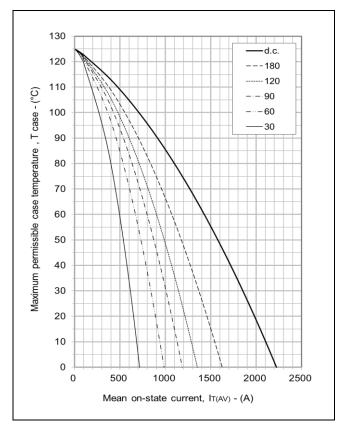
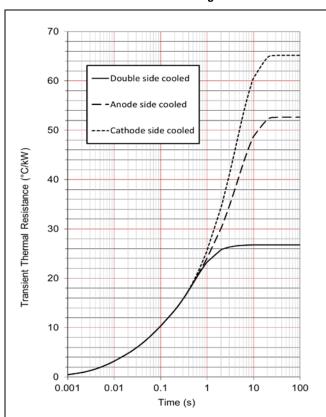


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



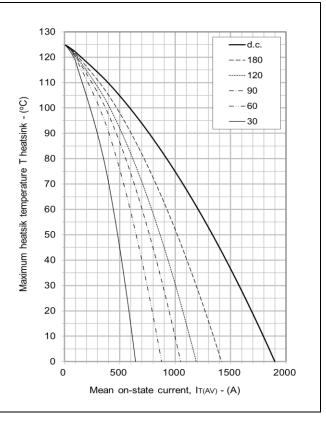


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	2.300	5.423	16.907	2.149
cooled	Ti(s)	0.007	0.046	0.496	1.825
Anode side	Ri(°C/kW)	2.321	5.266	10.269	34.803
cooled	Ti(s)	0.007	0.046	0.348	4.582
Cathode side	Ri(°C/kW)	2.490	5.911	7.426	49.343
cooled	Ti(s)	0.007	0.053	0.393	4.230

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th}[j-c]}$ when the device operates at conduction angles other than d.c.

Double side cooling] [,	Anode Side	C
	ΔZ_{th}	(z)	П		ΔZ_i	h
6°	sine.	rect.] [θ°	sine.	
180	4.15	2.72] [180	4.15	
120	4.90	4.02] [120	4.89	
90	5.74	4.79] [90	5.73	
60	6.53	5.65] [60	6.52	
30	7.16	6.64] [30	7.15	
15	7.46	7 18	1 [15	7 44	Г

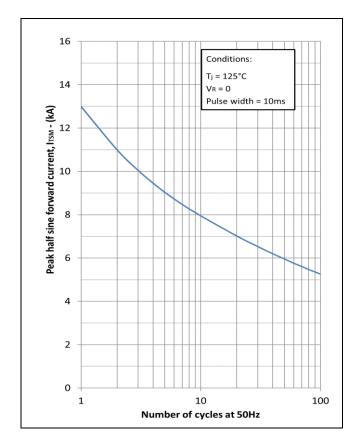
	Anode Side	Cooling	 Ca	ıtı
	ΔZ _{th} (z)			
θ°	sine.	rect.	θ°	
180	4.15	2.72	180	
120	4.89	4.02	120	
90	5.73	4.78	90	
60	6.52	5.65	60	
30	7.15	6.62	30	
1 5	7.44	7.16	15	Γ

Cathode Sided Cooling				
	ΔZ_{i}	$\Delta Z_{th}(z)$		
θ°	sine.	rect.		
180	4.13	2.71		
120	4.87	4.00		
90	5.69	4.76		
60	6.46	5.60		
30	7.07	6.56		
4.5	7.00	7.00		

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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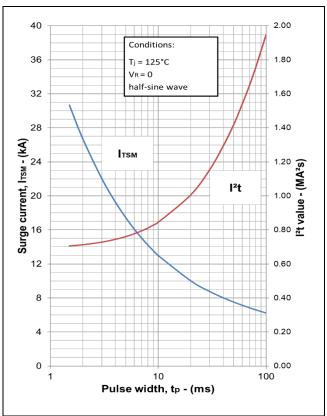


Fig. 10 Multi-cycle surge current

Fig. 11 Single-cycle surge current

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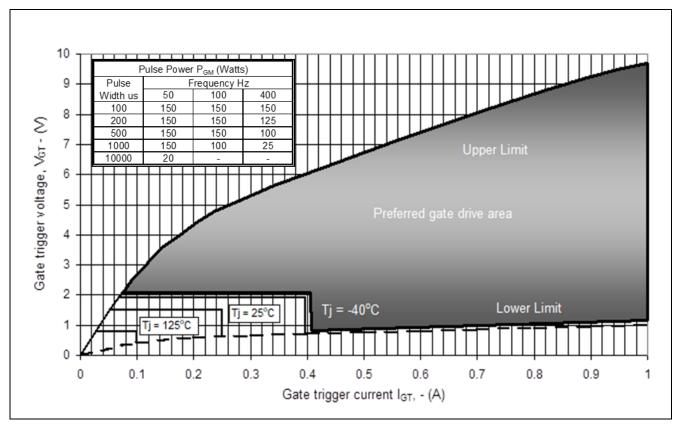


Fig. 12 Gate characteristics

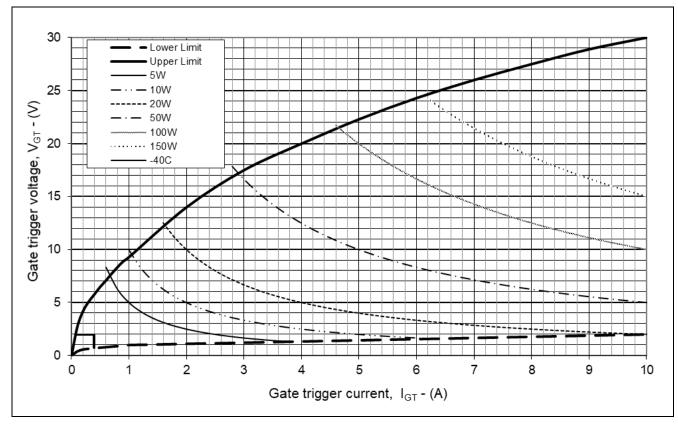


Fig. 13 Gate characteristics

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PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

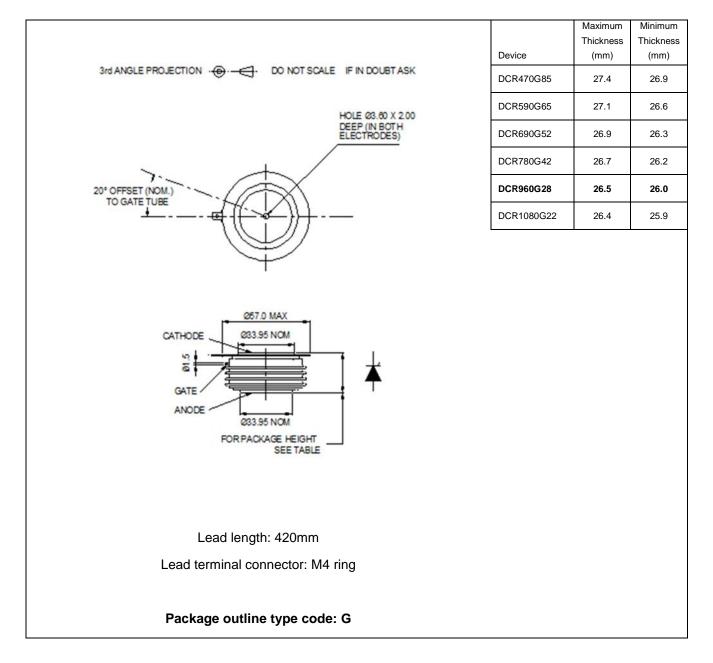


Fig. 14 Package outline

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